

Features

- Low drain-source on-resistance: $R_{DS(ON)}=0.14\Omega(\text{typ})$
- Easy to control gate switching
- Enhancement mode: $V_{th} = 2.5$ to $3.5V$
- 100% avalanche tested
- RoHS compliant

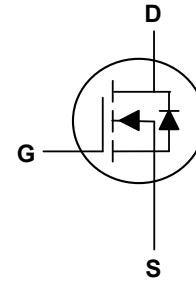
Key Performance Parameters



Parameter	Value	Unit
$V_{DS} @ T_{j,\max}$	650	V
$R_{DS(ON),\max}$	170	mΩ
I_D	20	A
$Q_{g,\text{typ}}$	38.5	nC
I_{DM}	60	A

Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)
- Charger, Lighting



Absolute Maximum Ratings($T_c=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	650	V
Gate-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current ¹	I_D	20	A
Pulsed Drain Current ²	I_{DM}	60	A
Single Pulse Avalanche Energy ⁴	E_{AS}	480	mJ
Avalanche Current	I_{AS}	3.5	A
Repetitive Avalanche energy, t_{AR} limited by $T_{J,\max}$	E_{AR}	0.7	mJ
MOSFET dv/dt ruggedness, $V_{DS} = 0 \dots 400V$	dv/dt	50	V/ns
Reverse diode dv/dt ³ $V_{DS}=0 \dots 400V$, $I_{SD} \leq I_D$		50	
Total Power Dissipation ($T_c=25^\circ\text{C}$)	P_D	150	W
Storage Temperature Range	T_{STG}	-55 to 150	°C
Operating Junction Temperature Range	T_J	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance Junction-Ambient	$R_{\theta JA}$	62	°C/W
Thermal Resistance Junction-Case	$R_{\theta JC}$	0.83	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}$, $I_D=250\mu\text{A}$	650	---	---	V
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}$, $I_D=10\text{A}$	---	140	170	$\text{m}\Omega$
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{GS}}=V_{\text{DS}}$, $I_D=250\mu\text{A}$	2.5	---	3.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{\text{DS}}=650\text{V}$, $V_{\text{GS}}=0\text{V}$, $T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{\text{DS}}=650\text{V}$, $V_{\text{GS}}=0\text{V}$, $T_J=150^\circ\text{C}$	---	---	100	
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 30\text{V}$, $V_{\text{DS}}=0\text{V}$	---	---	± 100	nA
Gate Resistance	R_G	$f = 1.0\text{MHz}$, open drain	---	8	---	Ω
Total Gate Charge	Q_g	$V_{\text{DD}}=400\text{V}$, $V_{\text{GS}}=10\text{V}$, $I_D=20\text{A}$	---	38.5	---	nC
Gate-Source Charge	Q_{gs}		---	8	---	
Gate-Drain Charge	Q_{gd}		---	15	---	
Turn-On Delay Time	$T_{d(\text{on})}$	$V_{\text{DD}}=400\text{V}$, $V_{\text{GS}}=10\text{V}$, $R_G=25\Omega$, $I_D=20\text{A}$	---	25	---	ns
Rise Time	T_r		---	59	---	
Turn-Off Delay Time	$T_{d(\text{off})}$		---	121	---	
Fall Time	T_f		---	44	---	
Input Capacitance	C_{iss}	$V_{\text{DS}}=100\text{V}$, $V_{\text{GS}}=0\text{V}$, $f=1\text{MHz}$	---	1724	---	pF
Output Capacitance	C_{oss}		---	72	---	
Reverse Transfer Capacitance	C_{rss}		---	6	---	

Drain-Source Diode Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Continuous Source Current	I_s	$T_c=25^\circ\text{C}$	---	---	20	A
Pulsed Source Current	I_{SM}		---	---	60	A
Diode Forward Voltage	V_{SD}	$V_G=0\text{V}$, $I_s=20\text{A}$, $T_J=25^\circ\text{C}$	---	0.9	1.2	V
Reverse Recovery Time	t_{rr}	$V_R=400\text{V}$, $I_F=20\text{A}$, $dI_F/dt=100\text{A}/\mu\text{s}$	---	453	---	ns
Reverse Recovery Charge	Q_{rr}		---	5.1	---	μC
Peak Reverse Recovery Current	I_{rrm}		---	22	---	A

Note:

1. Limited by $T_{j,\text{max}}$. Maximum Duty Cycle D = 0.50
2. Pulse width t_p limited by $T_{j,\text{max}}$
3. Identical low side and high side switch with identical R_G
4. $V_{\text{DD}}=50\text{V}$, $R_G=25\Omega$, $I_{AS}=3.5\text{A}$

Typical Characteristics

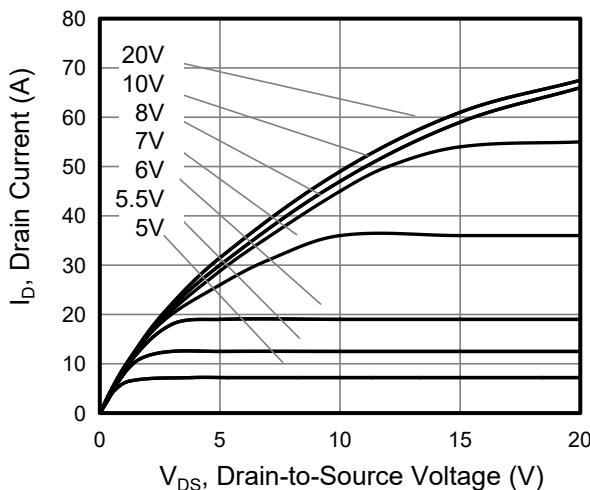


Figure 1. Output Characteristics

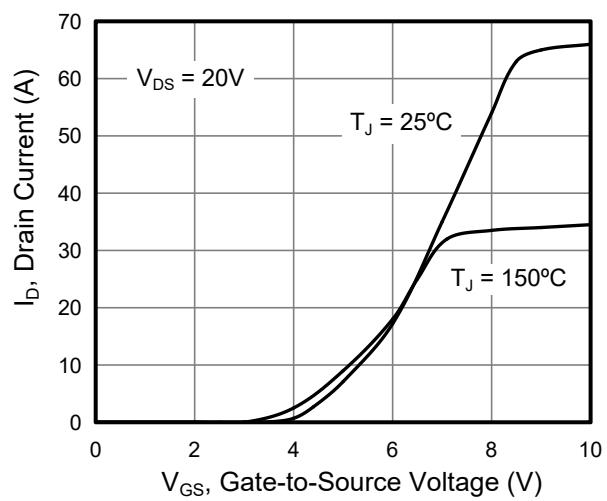


Figure 2. Transfer Characteristics

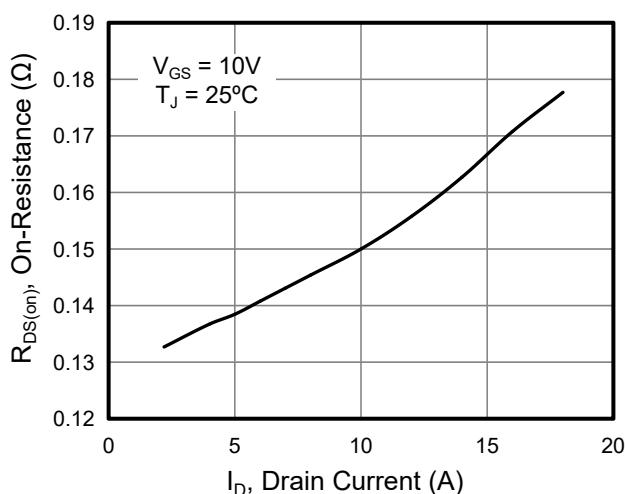


Figure 3. On-Resistance vs. Drain Current

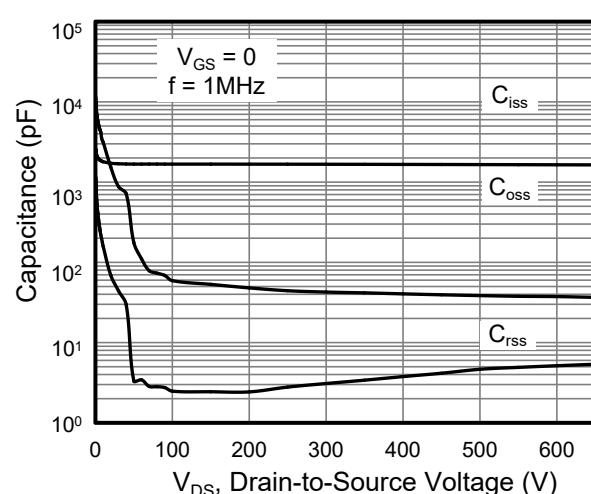


Figure 4. Capacitance

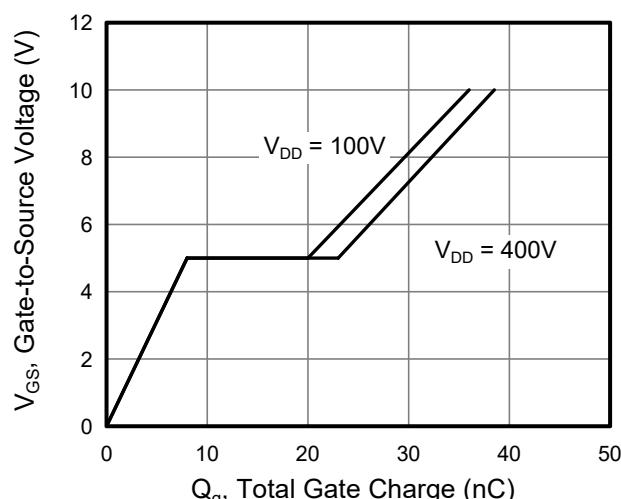


Figure 5. Gate Charge

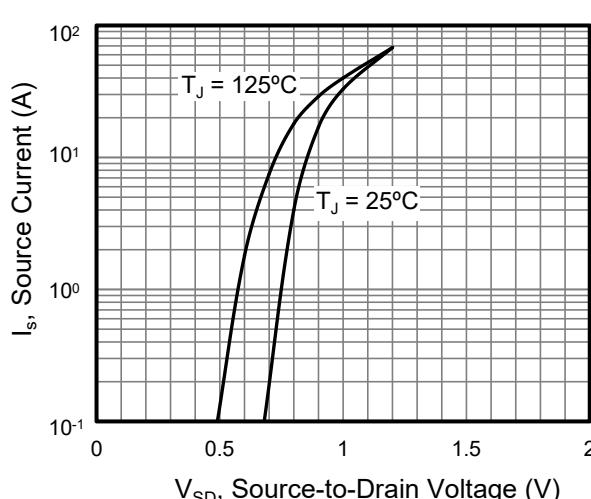


Figure 6. Body Diode Forward Voltage

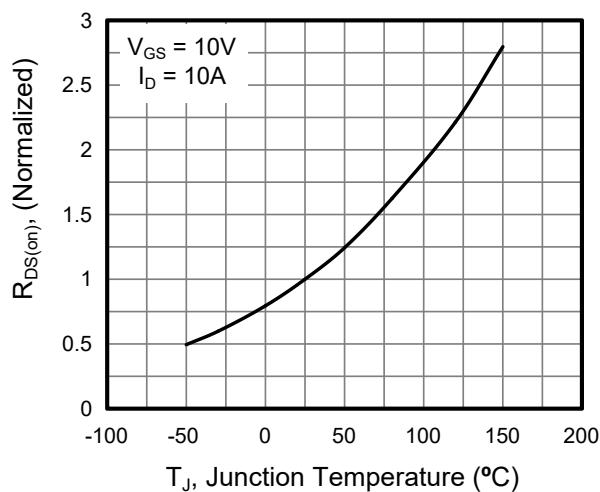


Figure 7. On-Resistance vs. Junction Temperature

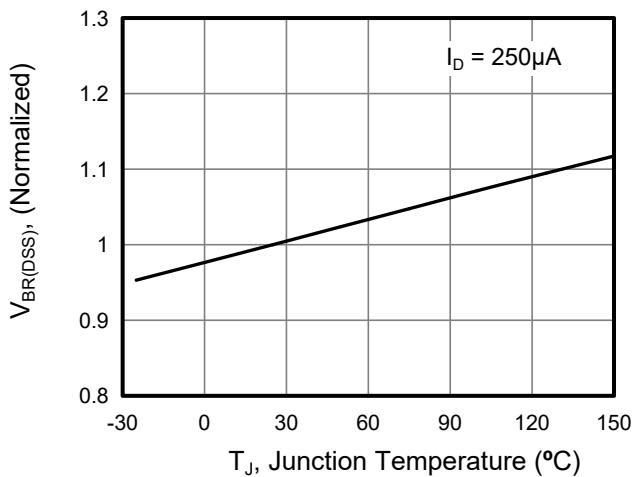


Figure 8. Breakdown voltage vs. Junction Temperature

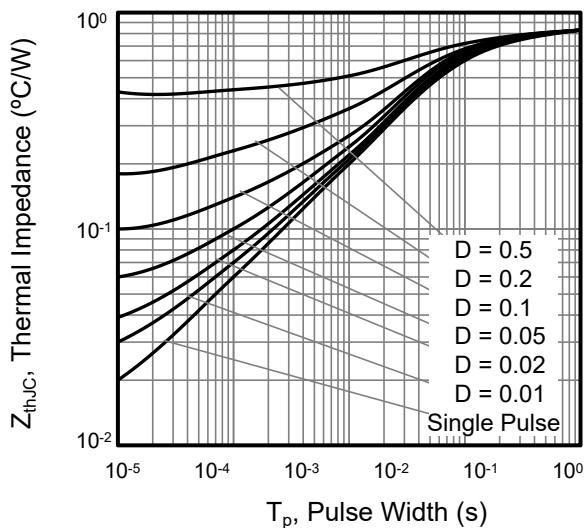
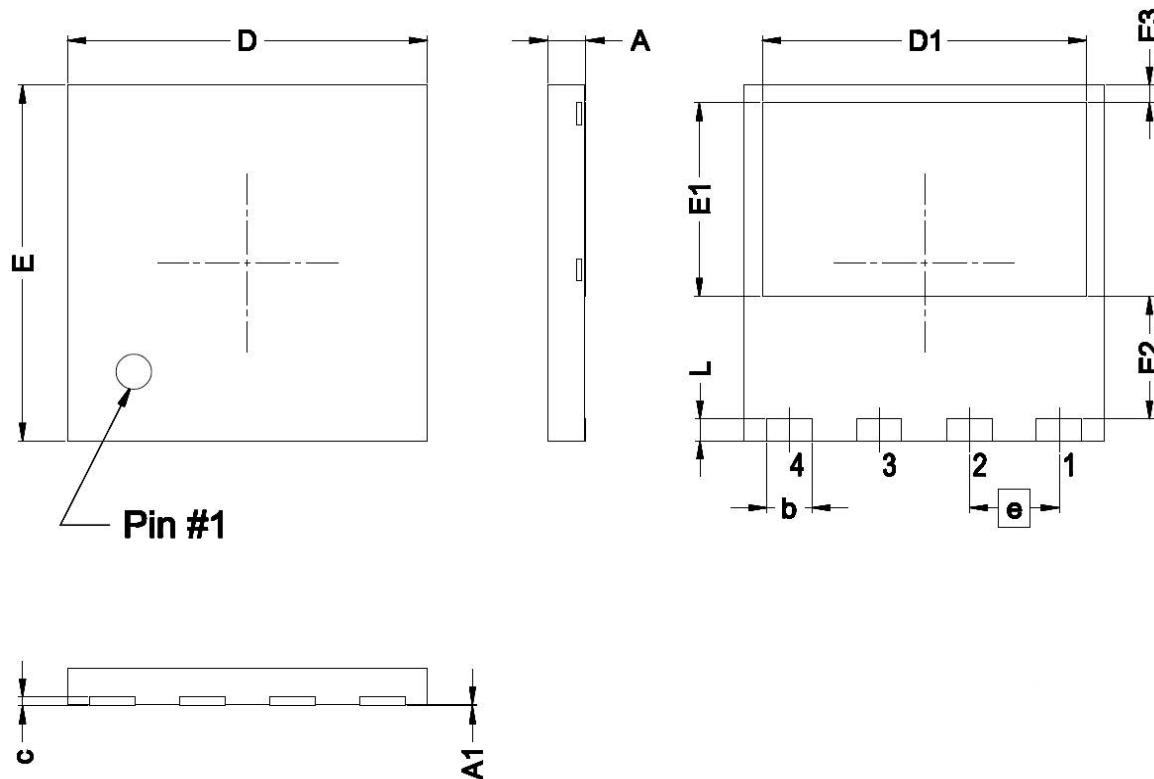


Figure 9. Transient Thermal Impedance

DFN8X8 Package Outline Dimensions



Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	0.75	0.85	0.95	E	7.90	8.00	8.10
A1	0.00		0.05	E1	4.20	4.35	4.45
b	0.90	1.00	1.10	E2	2.60	2.75	2.85
c	0.10	0.20	0.30	E3	0.30	0.40	0.50
D	7.90	8.00	8.10	e	2.00 BSC		
D1	7.10	7.20	7.30	L	0.40	0.50	0.60



Printing Information

ATC =====Brand

XXXXXXX =====Material Code

XXYY =====XX Representative Year
YY Representative Weeks